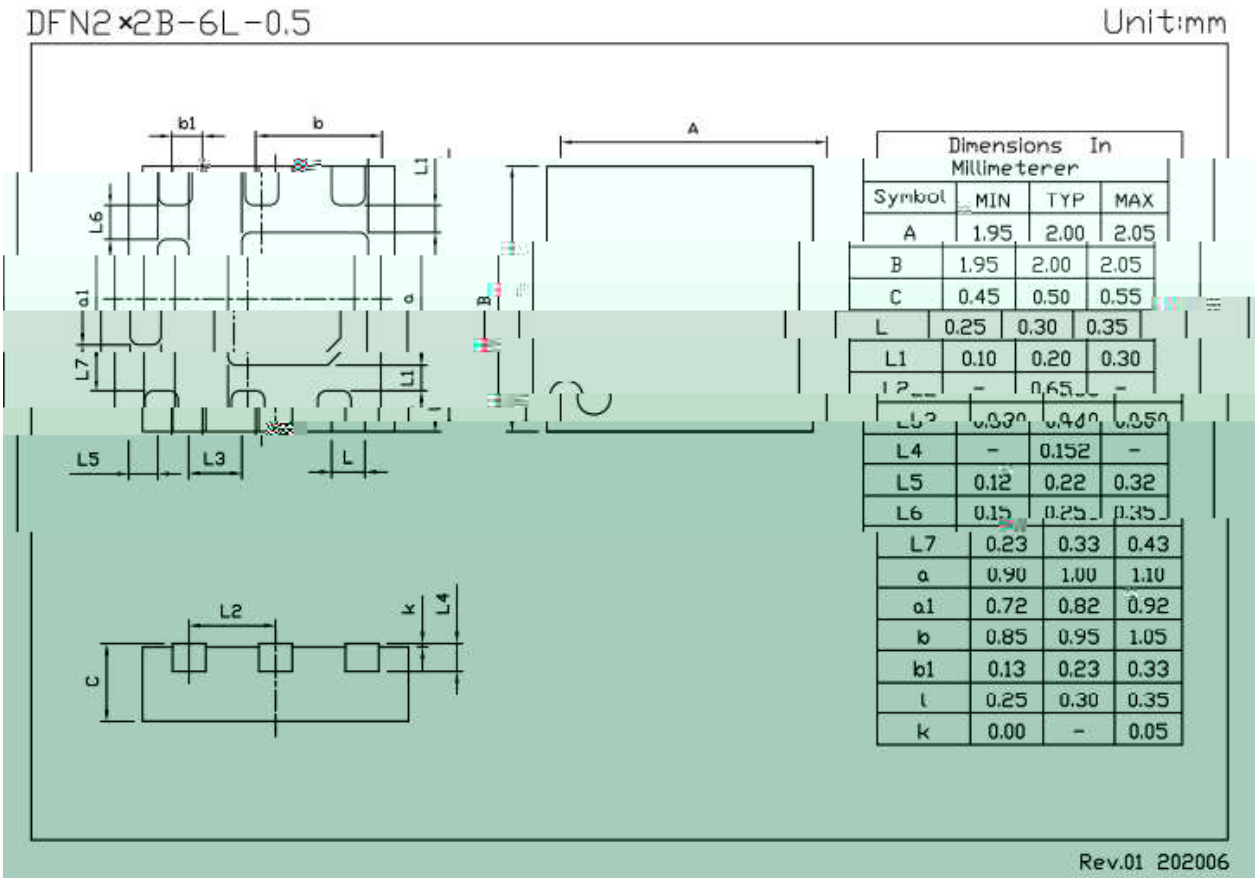
DFN 2×2B-6L P MOS
P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

V_{DS} (V) = -16V I_D = -11A
$R_{DS(ON)}$@-4.5V≤32mΩ
。HF Product.

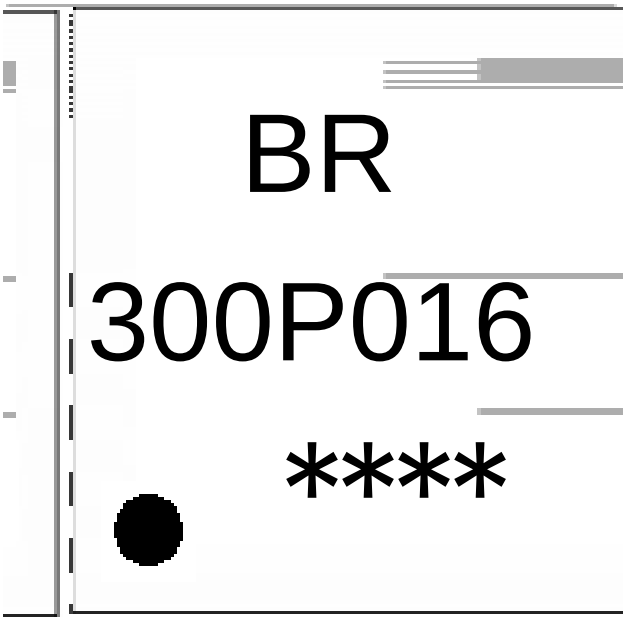
Power Management in Notebook computer, Portable Equipment and Battery powered systems.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I_D	-11	A
Pulsed Drain Current	I_{DM}	-44	A
Avalanche Current	I_{AS}	21	A
Avalanche energy L=0.5mH	E_{AS}	308	mJ
Power Dissipation for Single Operation	P_D	15.5	W
Maximum Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃
Thermal Resistance-Junction to Ambient	$R_{\theta JC}$ t 10s	8	℃/W

DFN2×2B-6L-0.5 外形尺寸图



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	-	0.65	-
L3	0.30	0.40	0.50
L4	-	0.152	-
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	-	0.05



BR

300P016

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Note:

BR:	Company Code
300P016:	Product Type
****:	Lot No. Code, code change with Lot No

Note: